

30V N-ch Power MOSFET

General Features

- Proprietary New Trench Technology
- $R_{DS(ON),typ.}=4.0m\Omega@V_{GS}=10V$
- Low Gate Charge Minimize Switching Loss
- Fast Recovery Body Diode

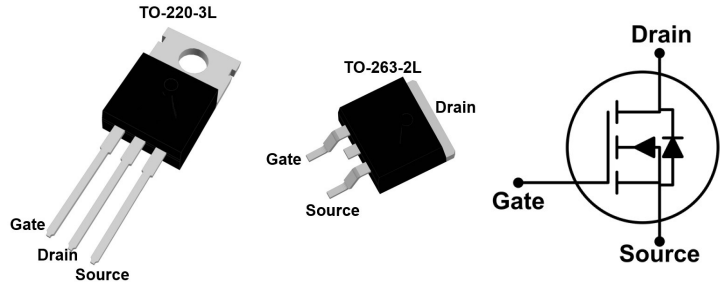
BV_{DSS}	$R_{DS(ON),max.}$	$I_D^{[2]}$
30V	5.2m Ω	104A

Applications

- High efficiency DC/DC Converters
- Synchronous Rectification
- UPS Inverter

Ordering Information

Part Number	Package	Marking
FTP30N5P2L	TO-220-3L	30N5P2L
FTB30N5P2L	TO-263-2L	30N5P2L



Absolute Maximum Ratings

$T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Unit
V_{DSS}	Drain-to-Source Voltage ^[1]	30	V
V_{GSS}	Gate-to-Source Voltage	± 20	
I_D	Continuous Drain Current ^[2]	104	A
	Continuous Drain Current ^[3]	48	
	Continuous Drain Current at $T_C=100^\circ\text{C}$ ^[2]	74	
I_{DM}	Pulsed Drain Current at $V_{GS}=10V$ ^[2,4]	418	
P_D	Power Dissipation	101	W
	Derating Factor above 25°C	0.67	W/ $^\circ\text{C}$
T_L	Soldering Temperature	300	$^\circ\text{C}$
	Distance of 1.6mm from case for 10 seconds		
T_J & T_{STG}	Operating and Storage Temperature Range	-55 to 175	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.

Thermal Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case			1.5	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient			63	

Electrical Characteristics

OFF Characteristics

 $T_J=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30			V	$V_{GS}=0V, I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current			1	μA	$V_{DS}=24V, V_{GS}=0V$
I_{GSS}	Gate-to-Source Leakage Current			± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$

ON Characteristics

 $T_J=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	--	4.0	5.2	m Ω	$V_{GS}=10V, I_D=80A^{[5]}$
		--	5.3	7.4	m Ω	$V_{GS}=4.5V, I_D=52A^{[5]}$
$V_{GS(TH)}$	Gate Threshold Voltage	1.0	--	3.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$

Note:

[1] $T_J=25^{\circ}\text{C}$ to 175°C

[2] Silicon limited current only

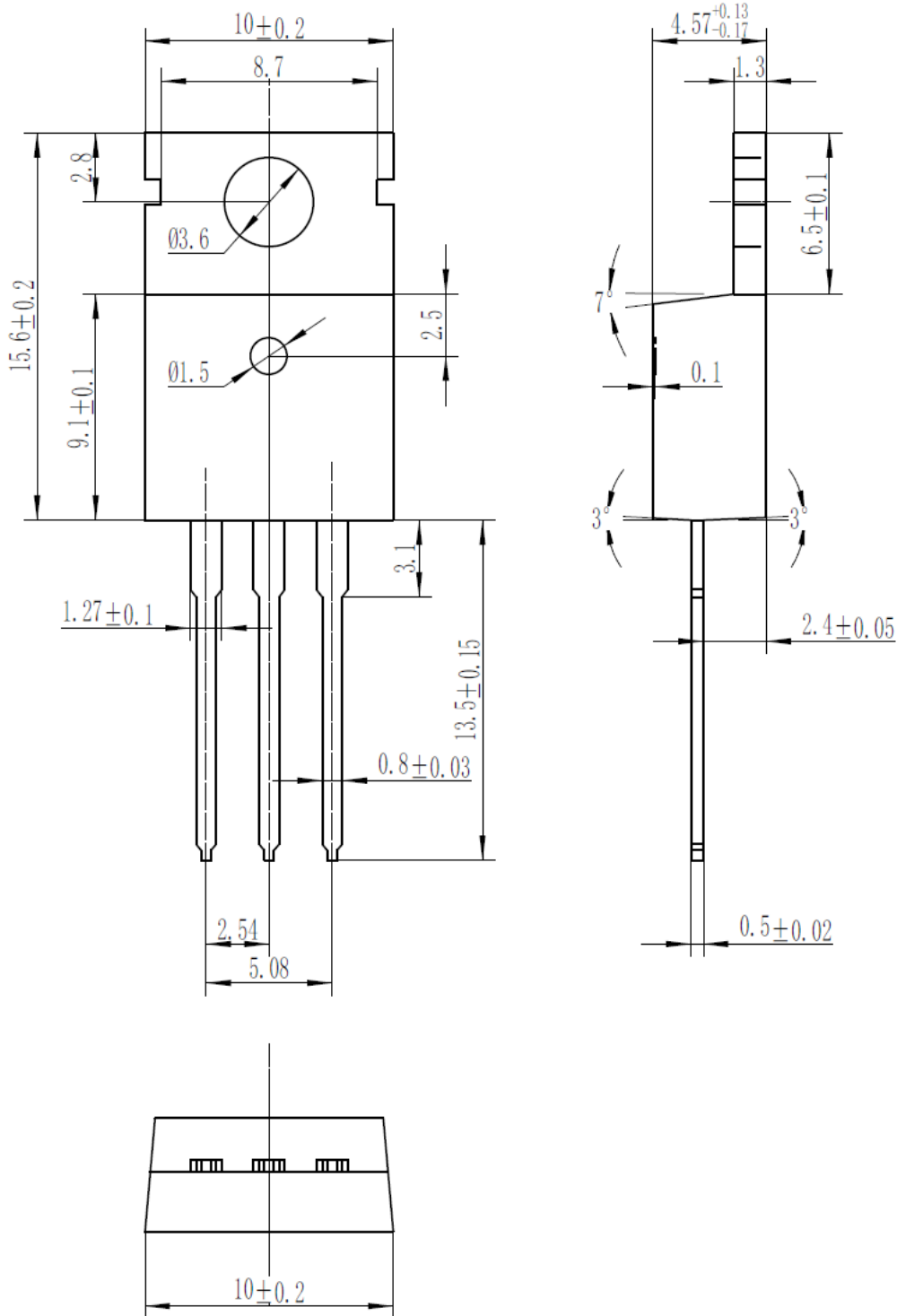
[3] Package limited current

[4] Repetitive rating, pulse width limited by maximum junction temperature.

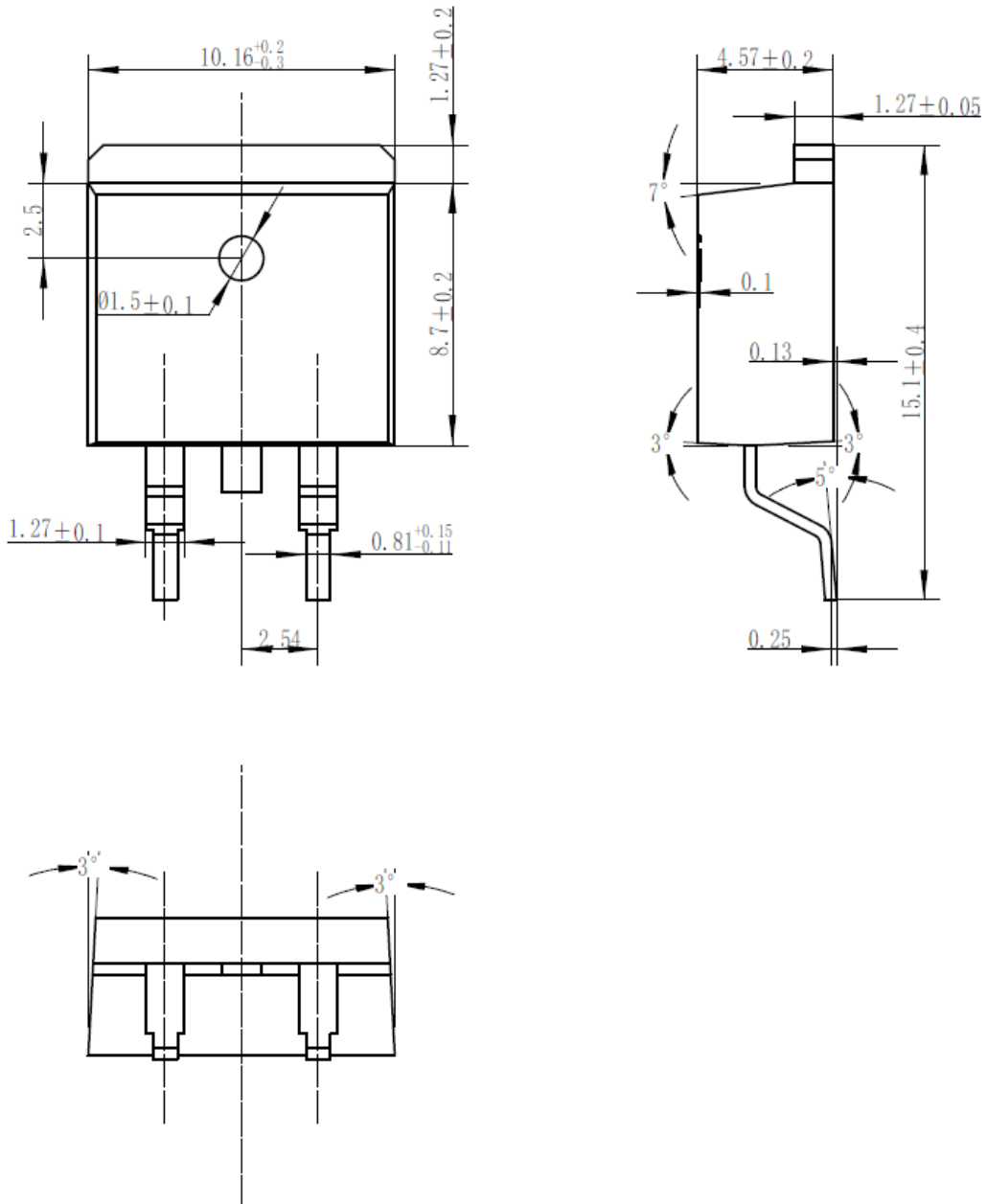
[5] Pulse width $\leq 380\mu s$; duty cycle $\leq 2\%$.

Package Dimensions

TO-220-3L



TO-263-2L





Published by

ARK Microelectronics Co., Ltd.

ADD: 4F,D26,UESTC National Science Park No. 1 Shuangxing Avenue, Gongxing Street ,Shuangliu District, Chengdu, China (Sichuan) Pilot Free Trade Zone.

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